2	286 43 75287	planariza\$5) platen same ring same (CMP polish\$3	USPAT EPO; JPO:	Time stamp 2003/11/02 16:37
2		platen same ring same (CMP polish\$3	PDQ. TDQ	
2 -		platen same ring same (CMP polish\$3	DDG. TDG	
-	75287	-3	LEPO; JPO;	2003/11/02 16:37
-	75287	planariza\$5)	DERWENT	
j			USPAT	2003/10/31 14:56
		abrading		20,02 2,100
-	5296		USPAT	2003/10/31 14:59
1		abrading) and (sens\$3) same (thermocouple	}	1
1		temperature ir infrared optical)		
-	2725		USPAT	2003/10/31 15:00
		abrading) and (sens\$3) same (thermocouple		1
1 1		temperature ir infrared optical)) and	ĺ	(
		(wafer semiconductor)	J]
~	16724		USPAT	2003/10/31 15:00
1 1		abrading) and (sens\$3) or (thermocouple		1
		temperature ir infrared optical)) same		
1	7077	(platen \$4table pad cloth)		
1	7077		USPAT	2003/10/31 15:01
1 1		abrading) and((sens\$3) or (thermocouple temperature ir infrared optical)) same	Í	(
1		(platen \$4table pad cloth)) and (wafer		J .
		semiconductor)		ĺ
_	1213	(((planarization or polishing or lapping	USPAT	
	1215	or abrading) and ((sens\$3) or	USPAT	2003/10/31 15:08
	ĺ	(thermocouple temperature ir infrared		
		optical)) same (platen \$4table pad cloth))		l
[and (wafer semiconductor)) and (451/\$		
	ļ	156/345.\$)		
-	47	(platen turntable cloth) same (sens\$3)	USPAT	2003/10/31 15:14
1	- 1	same (ir infrared thermocouple	001111	2003/10/31 13:14
		temperature) same (polish\$3 abrad\$3 lap\$4		1
	1	planarization)		
-	439	(platen turntable cloth) with (sens\$3) same	USPAT	2003/10/31 15:33
ĺ	[(ir infrared thermocouple temperature)	· · · · · · ·	
-		156/345.14 156/345.15	USPAT	2003/10/31 15:38
	40	156/345.16	USPAT	2003/10/31 15:38